

1988 GaAs REL WORKSHOP PROGRAM
NOVEMBER 6, 1988 OPRYLAND HOTEL, NASHVILLE, TN

SESSION I MMIC RELIABILITY Ed Hakim, Session Chairman

RELIABILITY CHARACTERIZATION OF A PRODUCTION GaAs MMIC AMPLIFIER -
METHODOLOGY AND RESULTS; Michael F. Peters and Anthony L. Rubalcava - TriQuint Semiconductor,

SINGLE PULSE RF DAMAGE TESTS ON GaAs MMICS.

John H. McAdoo, Robert Seeley, W.T. Anderson, J. A. Roussos, and W. Michael Bollen

RELIABILITY EVALUATION OF A 0.5 μ m SELF-ALIGNED PROCESS FOR GaAs MMICS;

John Chickanosky - Sanders Associates.

OBSERVATION OF PREMATURE DRAIN-SOURCE BREAKDOWN IN HETEROJUNCTION FETS;

E. Martin, O Aina, A. Iliadis, H. Hier, A. Fathimulla.

ON THE RELIABILITY OF ENHANCED BARRIER SCHOTTKY CONTACTS TO n-InP FOR POWER APPLICATIONS;

A. Iliadis, W. Lee

SESSION II MATERIALS AND DEVICE RELIABILITY Bill Roesch, Session Chairman

ON THE NATURE OF "M" TRAPS IN MBE GROWN GaAs;

Dimitris E. Ioannou and Yu-Juiig Huang – Electrical Engineering Department, University of Maryland,

HIGH EFFICIENCY AND HIGHLY RELIABLE GaAs HIGH POWER FET,

S. Sakamoto, N. Kasai, T. Sonoda, T. Sakayori, M. Wataze, S. Igi, M. Yamanouchi, S. Takamiyu,
and S. Mitsui - Kita-Itami Works, Mitsubishi Electric Corporation.

RELIABILITY OF HIGH BURNOUT GaAs MONOLITHIC SCHOTTKY JUNCTION PAIRS FOR W-BAND MIXERS,

Aimad - M/A-COM, W. T. Anderson and A. Christou - Naval Research Laboratory.

GaAs FET RELIABILITY INVESTIGATED THROUGH HIGH TEMPERATURE STORAGE TESTS ON WAFERS;

Jeff Parker, John Mahon, and Jean-Pierre Lanteri - M/A-COM Advanced Semiconductor Division.

SESSION III MODFET RELIABILITY Ken Russell, Session Chairman

DEGRADATION MECHANISMS OF GaAs HEMTS;

D. J. LaCombe and W. W. Hu - General Electric Company, Syracuse, New York.

AlNAs/GaInAs HEMT HIGH TEMPERATURE STORAGE TESTS,

Robert J. Ferro and Umesh K. Mishra – Hughes Research Laboratories.

DLTS STUDY OF HEMT FAILURE MECHANISMS.

R. Magno, R. Shelby, and W. T. Anderson - Naval Research Laboratory.

MODELLING OF HEMT FAILURE MECHANISMS-, F. A. Buot and W. T. Anderson - Naval Research Laboratory,

Washington, DC 20375-5000.

SESSION IV RADIATION EFFECTS Walter Koziarz, Session Chairman

COMPARISON OF DCFL, BFL, AND SDFL GaAs LOGIC CIRCUITS EXPOSED TO NEUTRON IRRADIATION;

Bruce Janousek, Bill Yamada, Mary Rosenbluth, and Walter Bloss - The Aerospace Corporation.

PHOTOVOLTAIC SIGNAL GENERATION IN HETEROJUNCTION AND HOMOJUNCTION FETs DUE TO PULSED

IONIZING RADIATION; S. B. Witmer, R. L. Remke and S. D. F. Jones - AT&T Bell Laboratories, PA, R. Zuleeg -
McDonnell Douglas.

EFFECT OF BACKGROUND DOPANT CONCENTRATION ON NEUTRON DEGRADATION OF MODFETS.

M. J. O'Loughlin, R. J. Krantz, W. L. Bloss, and B. K. Janousek - The Aerospace Corporation.